

Title of Change:	Hydrazine elimination of ON Semiconductor Niigata Co., Ltd. (OSNC) and change to copper wire material.			
Proposed first ship date:	22 November 2018			
Contact information:	Contact your local ON Semiconductor Sales Office or < <u>Tetsuya.Fukushima@onsemi.com</u> >			
Samples:	Contact your local ON Semiconductor Sales Office.			
Type of notification:	This is an Initial Product/Process Change Notification (IPCN) sentto customers. IPCNs are issued at least 3 days prior to the issuance of the Final Change Notice (FPCN). An IPCN is an advance notification about a upcoming change and contains general information regarding the change details and devices affected. It als contains the preliminary reliability qualification plan. The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN). This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 90 days prior to implementation of the change. In case of questions, contact <pcn.support@onsemi.com>.</pcn.support@onsemi.com>			
Change Part Identification:	Date Code			
Change category:	🛛 Wafer Fab Change 🛛 Assembly Change	Test Change Other		
Change Sub-Category(s):Image: Material ChangeImage: Manufacturing Site Change/AdditionImage: Product specific changeImage: Manufacturing Process ChangeImage: Manufacturing Process Change		<ul> <li>Datasheet/Product Doc change</li> <li>Shipping/Packaging/Marking</li> <li>Other:</li> </ul>		
Sites Affected:	ON Semiconductor Sites: ON Carmona, Philippines ON Niigata, Japan	External Foundry/Subcon Sites: None		
The related products are transfe	es the elimination of Hydrazine in ON Semiconductor erred to a process that does not use Hydrazine on the ion between the chip and the lead from Gold wire to Before Change Description			
Fab (OSNC)	N1 Fab (Minimum rule=0.8um, Class=100)	N1 Fab (Minimum rule=0.8um, Class=100) AND N2 Fab (Minimum rule=0.25um, Class=10)		
Wire material	Aluminum (without Anti-reflected Layer)	Aluminum (with Anti-reflected Layer)		
wite material		Silicon nitride and Silicon oxide or Oxide		
Interlayer material	Silicon nitride and Polyimide or Polyimide			
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QV DEVICE NAM PACKAGE:	E: <u>LB11870-TRM-E</u> <u>HSSOP48 (375 mil)</u>			
Test	Specification	Condition	Interval	
HTOL	JESD22-A108	Tj=150°C, 100 % max rated Vcc	1008 hrs	
HTSL	JESD22-A103	Ta= 150°C	1008 hrs	
TC	JESD22-A104	Ta= -65°C to +150°C	500 сус	
тнв	JESD22-A101	85°C, 85% RH, bias	1008 hrs	
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig,	96 hrs	
PC	J-STD-020 JESD-A113	MSL 3 @ 260 °C	-	
HBM	JS001	100pF,1.5kohm	-	
CDM	JS002		-	
fected Standa	d Part:			
Part Number		Qualifi	Qualification Vehicle	
LB1909MC-BH			LB11870-TRM-E	

## Appendix A: Changed Products

Product	Customer Part Number	Qualification Vehicle
LB1909MC-BH		LB11870-TRM-E